

**512K (64K x 8) CMOS ROM**

- **VERY FAST ACCESS TIME** : 100 ns  
(Chip select or address access time)
- **LOW POWER "CMOS" CONSUMPTION** :
  - Operating current 40mA Max
  - Stand by current 20µA Max
- **SINGLE +5V ± 10% POWER SUPPLY.**
- **STATIC OPERATION.**
- **INPUTS AND OUTPUTS TTL COMPATIBLE.**
- **THREE STATE OUTPUTS.**
- **MASK PROGRAMMABLE ACTIVE LOW/HIGH  $\overline{CE}$ .**
- **AUTOMATIC POWER DOWN.**

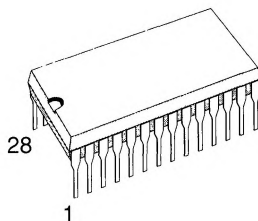
**DESCRIPTION**

The M23C512 is a 524,288 bit, CMOS Masked Read Only Memory (ROM), organized as 65,536 x 8 bits. It is manufactured in 1.2 micron CMOS technology : Very fast access time of 100 ns makes it ideal for EPROM replacement on high performance, high volume running applications. This device features a Two Line Control system : Chip select line (CE) is active low or active high by mask programming, as per user's choice. When not active, it brings the device into standby mode, making it suitable for battery operated systems. Output Enable is to be used for Output control.

After cycle completion and 50ns without input change, the M23C512 automatically goes into power-down mode ( $I_{CC} = 1$  mA), the data remaining latched on the output.

**PIN FUNCTIONS**

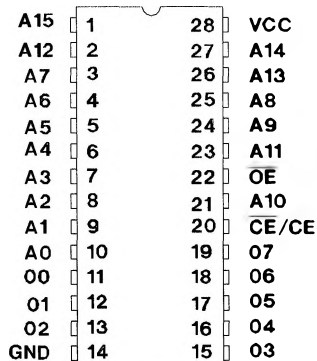
|                      |                   |
|----------------------|-------------------|
| A0-A15               | ADDRESS INPUTS    |
| O0-O7                | DATA OUTPUTS      |
| CE / $\overline{CE}$ | CHIP ENABLE INPUT |
| $\overline{OE}$      | OUTPUT ENABLE     |
| V <sub>CC</sub>      | +5V POWER SUPPLY  |
| GND                  | GROUND            |



PDIP-28

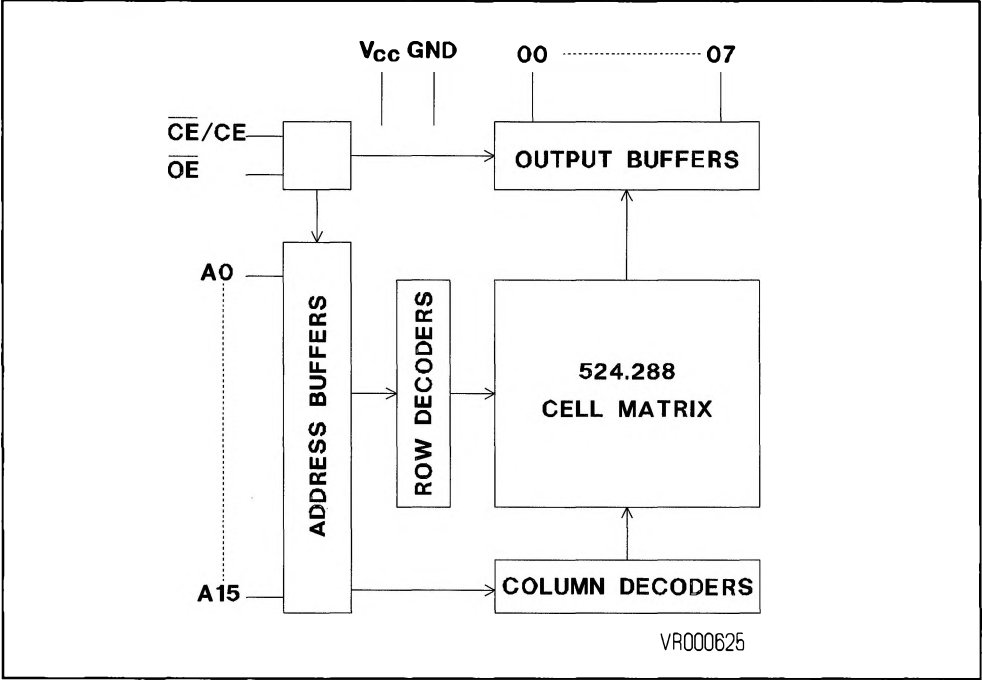
(Ordering information at the end of the datasheet)

**Figure 1 : Pin Connection**



VR00B231

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

| Symbol            | Parameter                                       | Value        | Unit |
|-------------------|-------------------------------------------------|--------------|------|
| V <sub>CC</sub>   | Supply voltage with respect to Ground           | -0.5 to +7.0 | V    |
| V <sub>i</sub>    | Input or Output voltages with respect to Ground | -0.5 to +7.0 | V    |
| T <sub>amb</sub>  | Operating temperature range                     | 0 to +70     | °C   |
| T <sub>bias</sub> | Temperature range under bias                    | 0 to + 125   | °C   |
| T <sub>stg</sub>  | Storage temperature                             | -65 to +150  | °C   |

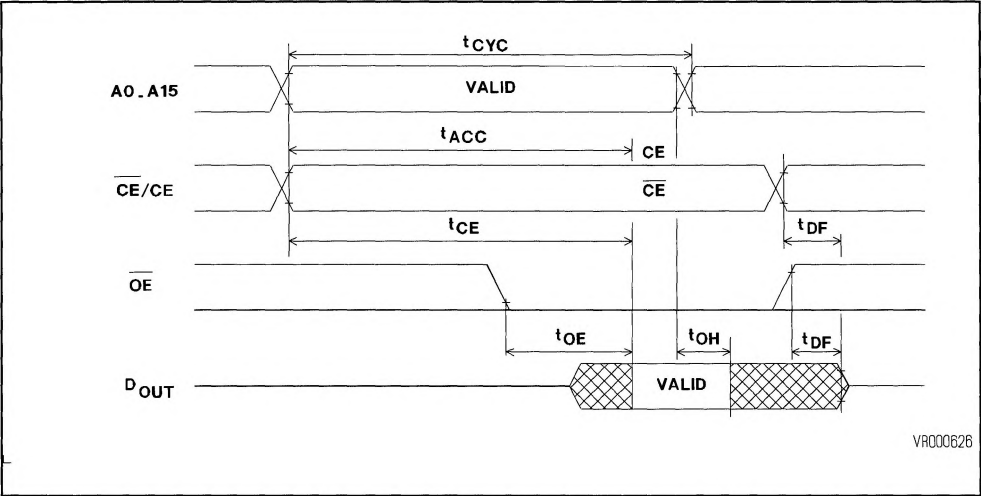
NOTE : Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation to these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rated conditions for extended periods of time may affect device reliability.

AC TEST CONDITIONS

Input Rise and Fall Times : ≤ 10 ns  
Input Levels : 0.45V and 2.4V

Timing Measurement Reference Levels :  
Inputs : 0.8V and 2.0V - Outputs : 0.8V and 2.0V

TIMING WAVEFORMS



OPERATION MODES

| MODE           | CE | or (CE) | OE (Note 1) | OUTPUT           |
|----------------|----|---------|-------------|------------------|
| READ           | L  | (H)     | L           | D <sub>OUT</sub> |
| STANDBY        | H  | (L)     | X           | HIGH Z           |
| OUTPUT DISABLE | L  | (H)     | H           | HIGH Z           |

DC CHARACTERISTICS

T<sub>AMB</sub> = 0°C to 70°C V<sub>CC</sub> = 5V ± 10%

| Symbol           | Parameter                              | Test Condition                                                   | Value |                       | Unit |
|------------------|----------------------------------------|------------------------------------------------------------------|-------|-----------------------|------|
|                  |                                        |                                                                  | Min   | Max                   |      |
| I <sub>LI</sub>  | Input Leakage current                  | V <sub>IN</sub> = 0 V to V <sub>CC</sub>                         | -10   | 10                    | μA   |
| I <sub>LO</sub>  | Output Leakage current                 | V <sub>IN</sub> = 0 V to V <sub>CC</sub>                         | -10   | 10                    | μA   |
| I <sub>CC1</sub> | V <sub>CC</sub> Active Current         | CE = OE = V <sub>IL</sub> , I <sub>OUT</sub> = 0 mA (f = 10 MHz) |       | 40                    | mA   |
| I <sub>CC1</sub> | V <sub>CC</sub> Active Current         | CE = OE = V <sub>IL</sub> , I <sub>OUT</sub> = 0 mA (f = 5 MHz)  |       | 20                    | mA   |
| I <sub>CC2</sub> | V <sub>CC</sub> Standby Current - TTL  | CE = V <sub>IH</sub>                                             |       | 1                     | mA   |
| I <sub>CC3</sub> | V <sub>CC</sub> Standby Current - CMOS | CE > V <sub>CC</sub> - 0.2V                                      |       | 20                    | μA   |
| V <sub>IL</sub>  | Input Low Voltage                      |                                                                  | -0.5  | 0.8                   | V    |
| V <sub>IH</sub>  | Input High voltage                     |                                                                  | 2.0   | V <sub>CC</sub> + 1.0 | V    |
| V <sub>OL</sub>  | Output Low voltage                     | I <sub>OL</sub> = 3.2 mA                                         |       | 0.4                   | V    |
| V <sub>OH</sub>  | Output High Voltage                    | I <sub>OH</sub> = -400 uA                                        | 2.4   |                       | V    |

NOTE 1 : OE may be active high by mask programming.

AC CHARACTERISTICS

| Symbol                         | Parameter                 | Test Condition            | Values |     | Unit |
|--------------------------------|---------------------------|---------------------------|--------|-----|------|
|                                |                           |                           | Min    | Max |      |
| T <sub>CYC</sub>               | Cycle Time                |                           |        | 100 | ns   |
| T <sub>ACC</sub>               | Address Access Time       | CE = V <sub>IL</sub>      |        | 100 | ns   |
| T <sub>CE</sub>                | Chip Enable Access Time   | CE = V <sub>IL</sub>      |        | 100 | ns   |
| T <sub>OE</sub>                | Output Enable Access Time | CE = OE = V <sub>IL</sub> |        | 50  | ns   |
| T <sub>DF</sub> <sup>(1)</sup> | CE High to Output float   |                           |        | 30  | ns   |
| T <sub>OH</sub>                | Output Hold               |                           | 10     |     | ns   |

CAPACITANCE <sup>(1)</sup>  
(T<sub>AMB</sub> = 25°C f = 1 MHz)

| Symbol           | Parameter          | Test Condition        | Max. | Unit |
|------------------|--------------------|-----------------------|------|------|
| C <sub>IN</sub>  | Input Capacitance  | V <sub>IN</sub> = 0V  |      | 5 pF |
| C <sub>OUT</sub> | Output Capacitance | V <sub>OUT</sub> = 0V |      | 5 pF |

NOTE 1 : This parameter is only sampled and not 100 % tested

ORDERING INFORMATION

| Part Number | Access Time | Supply Voltage | Temp.Range | Package |
|-------------|-------------|----------------|------------|---------|
| M23C512B1   | 100 ns      | 5V ± 10%       | 0 to +70°C | PDIP28  |

PACKAGE MECHANICAL DATA  
28-PIN -PLASTIC DIP

